



## FEATURES:

- Bar code reader / fine line sensor
- 0.007" - 0.013" resolution
- Compact size
- Glass lens

## PRODUCT DESCRIPTION

Opto Technology's OTR 680/690 series combines two emitters, a lens and photodetector into one low cost plastic housing. The rectangular aperture inside the package offers high resolution with good depth of field. The OTR 680 has two 940nm infrared emitting diodes with PIN Diode or Phototransistor and the OTR 690 series has two 660nm visible light emitting diodes with either sensor option. Custom apertures for these devices are available upon request.

## ABSOLUTE MAXIMUM RATINGS

### General

Storage Temperature Range ----- -55°C to +100°C  
 Operating Temperature Range ----- -40°C to +85°C  
 Lead Soldering Temperature (1/16" from case  
 for 5 seconds soldering iron, 10 seconds flow soldering) ----- 260°C

### Infrared Emitter (940 nm)

Reverse Voltage ----- 5 V  
 Continuous Forward Current ----- 50 mA  
 Power Dissipation ----- 100 mW

### Visible Emitter (660 nm)

Reverse Voltage ----- 5 V  
 Continuous Forward Current ----- 50mA  
 Power Dissipation ----- 100 mW

### Phototransistor

Collector-Emitter Voltage ----- 35 V  
 Emitter-Collector Voltage ----- 6 V  
 Power Dissipation (Derate 2.4 mW/°C above 25°C) ----- 250 mW

### PIN Diode

Reverse Voltage ----- 35V  
 Dark Current  $V_f=20V$  ----- 150nA  
 Power Dissipation (Derate 1.5 mW/°C above 25°C) ----- 150 mW



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### Infrared Emitter

Parameter	Symbol	Min	Typ	Max	Units
Forward Voltage ( $I_F = 50 \text{ mA}$ )	$V_F$		1.3	1.45	V
Reverse Current ( $V_R = 5 \text{ V}$ )	$I_R$			100	$\mu\text{A}$
Peak Wavelength ( $I_F = 20 \text{ mA}$ )	$\lambda_P$		940		nm
Radiant Intensity ( $I_F = 20 \text{ mA}$ )	$I$	1.3	2.5		mW/sr
Spectral Bandwidth at 50% ( $I_F = 20 \text{ mA}$ )	$\Delta\lambda$		50		nm
Half Intensity Beam Angle	$\theta$		10		Degrees

### Visible Emitter

Parameter	Symbol	Min	Typ	Max	Units
Forward Voltage ( $I_F = 20 \text{ mA}$ )	$V_F$		1.8	2.4	V
Reverse Current ( $V_R = 5 \text{ V}$ )	$I_R$			100	$\mu\text{A}$
Peak Wavelength ( $I_F = 20 \text{ mA}$ )	$\lambda_P$		660		nm
Luminous Intensity ( $I_F = 20 \text{ mA}$ )	$I_V$	250	500		mcd
Spectral Bandwidth at 50% ( $I_F = 20 \text{ mA}$ )	$\Delta\lambda$		20		nm
Half Intensity Beam Angle	$\theta$		10		Degrees

### Phototransistor

Parameter	Symbol	Min	Typ	Max	Units
Light Current ( $E_e=1.0\text{mW/cm}^2$ , $V_{CE}=5\text{V}$ )	$I_{CE(ON)}$	1	2.8		mA
Dark Current ( $E_e=0$ , $V_{CE}=10\text{V}$ )	$I_{CE0}$			60	nA
Saturation Voltage ( $I_C=1.0\text{mA}$ )	$V_{CE(SAT)}$			0.5	V
Rise Time ( $V_{CC}=5\text{V}$ , $R_L=100\Omega$ )	$T_r$		6		$\mu\text{s}$
Fall Time ( $V_{CC}=5\text{V}$ , $R_L=100\Omega$ )	$T_f$		8		$\mu\text{s}$

### Pin Diode

Parameter	Symbol	Min	Typ	Max	Units
Light Current ( $E_e=1.0\text{mW/cm}^2$ )	$I_L$	8	20		$\mu\text{A}$
Dark Current ( $E_e=0$ , $V_r=20\text{V}$ )	$I_D$			100	nA
Total Capacitance ( $V=0$ , $f=1 \text{ MHz}$ )	$C_t$		40		pF
Rise Time ( $R_L=1\text{k}\Omega$ )	$T_r$		1		$\mu\text{s}$
Fall Time ( $R_L=1\text{k}\Omega$ )	$T_f$		1		$\mu\text{s}$

### Coupled Characteristics

Parameter	Symbol	Min	Typ	Max	Units
Light Current ( $I_F = 20 \text{ mA}$ , $V_{CE} = 5 \text{ V}$ , $d = 0.22 \text{ in}$ , OTR680-X2X) <sup>1</sup>	$I_{CE(ON)}$	50			$\mu\text{A}$
Dark Current ( $I_F = 0 \text{ mA}$ , $V_{CE} = 5 \text{ V}$ , OTR680-X2X) <sup>2</sup>	$I_{CE0}$			40	nA
Light Current ( $I_F = 20 \text{ mA}$ , $V_{CC} = 5 \text{ V}$ , $d = 0.22 \text{ in}$ , OTR681-X2X) <sup>1</sup>	$I_{CE(ON)}$	0.10			$\mu\text{A}$
Dark Current ( $I_F = 0 \text{ mA}$ , $V_{CC} = 5 \text{ V}$ , OTR681-X2X) <sup>2</sup>	$I_{CE0}$			5	nA
Light Current ( $I_F = 20 \text{ mA}$ , $V_{CE} = 5 \text{ V}$ , $d = 0.22 \text{ in}$ , OTR690-X2X) <sup>1</sup>	$I_{CE(ON)}$	10			$\mu\text{A}$
Dark Current ( $I_F = 0 \text{ mA}$ , $V_{CE} = 5 \text{ V}$ , OTR690-X2X) <sup>2</sup>	$I_{CE0}$			40	nA
Light Current ( $I_F = 20 \text{ mA}$ , $V_{CC} = 5 \text{ V}$ , $d = 0.22 \text{ in}$ , OTR691-X2X) <sup>1</sup>	$I_{CE(ON)}$	0.02			$\mu\text{A}$
Dark Current ( $I_F = 0 \text{ mA}$ , $V_{CC} = 5 \text{ V}$ , OTR691-X2X) <sup>2</sup>	$I_{CE0}$			5	nA

<sup>1</sup> Reflecting surface is Eastman Kodak neutral white test card having a 90% diffused reflectance.

<sup>2</sup> No reflective surface

### Reflective Surface

Parameter	Symbol	Min	Typ	Max	Units
Element Contrast		(80%)			%
Diffused Reflectance		(90%)			%
Element Width ( 0.002x0.045 Aperture)	$W_N$	0.007			in
Narrow Element to Narrow Space Ratio			0.95		

Product Specifications ( $T_A = 25^\circ\text{C}$  unless noted)



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REV. O (01/00)

## ORDERING INFORMATION

